

TENTATIVE

TOSHIBA PHOTOCOUPLER GaAlAs IRED & PHOTO-IC

TLP250F

TRANSISTOR INVERTER

INVERTER FOR AIR CONDITIONOR

IGBT GATE DRIVE

POWER MOS FET GATE DRIVE

The Toshiba TLP250F consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP.

TLP250F is suitable for gate driving circuit of IGBT or power MOS FET.

- Input Threshold Current : $I_F = 5\text{mA}$ (Max.)
- Supply Current : 11mA (Max.)
- Supply Voltage : 10~35V
- Output Current : $\pm 1.5\text{A}$ (Max.)
- Switching Time : $t_{pHL}, t_{pLH} = 0.5\mu\text{s}$ (Max.)
- Isolation Voltage : $2500V_{rms}$ (Min.)
- UL Recognized : UL1577, File No.E67349
- Option (D4) type

VDE Approved : DIN VDE0884 / 06.92、認定No.76823

Maximum Operating Insulation Voltage : 1140V_{PK}

Highest Permissible Over Voltage : 6000V_{PK}

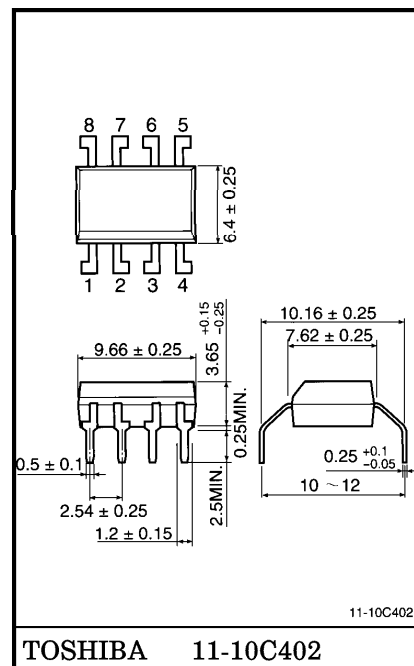
(Note 1) When a VDE0884 approved type is needed,
please designate the "Option (D4)"

- Structural Parameter
 - Creepage Distance : 8.0mm (Min.)
 - Clearance : 8.0mm (Min.)

TRUTH TABLE

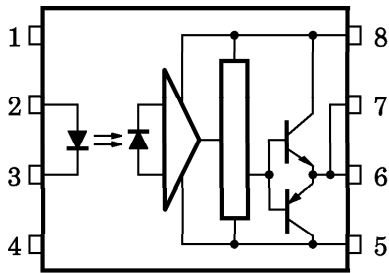
		Tr1	Tr2
Input LED	ON	ON	OFF
	OFF	OFF	ON

Unit in mm



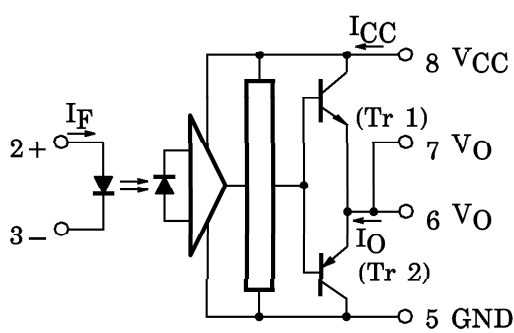
Weight : 0.54g

PIN CONFIGURATION (TOP VIEW)



- 1 : N.C.
- 2 : ANODE
- 3 : CATHODE
- 4 : N.C.
- 5 : GND
- 6 : V_O (OUTPUT) V_F
- 7 : V_O
- 8 : V_{CC}

SCHMATIC



(Note 2) A 0.1 μ F bypass capacitor must be connected between pin 8 and 5.

RESTRICTIONS ON PRODUCT USE

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